

905nm APD single tube series

SKU :GD5210Y-1-2-T046 / GD5210Y-1-5-T046 /GD5210Y-1-2-LCC3 /GD5210Y-1-5-LCC3

OVERVIEW

The device is a silicon avalanche photodiode with a spectral response range from visible to near infrared.

Peak response wavelength 905nm

FEATURES

Ortho-illuminated planar chip structure

High speed response

High gain

Low junction capacitance

Low noise

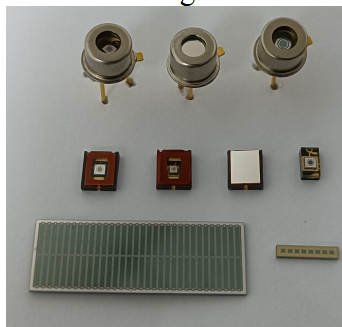
Customizable array size and photosensitive surface

APPLICATION

Laser Ranging

LIDAR

Laser Warning



OPTICAL CHARACTERISTICS (@Ta=22±3°C)

Model	GD5210Y -2-2-T046	GD5210Y -2-5-T046	GD5210Y -2-8-T046	GD5210Y -2-2- LCC3	GD5210Y -2-5- LCC3	GD5210Y -2-2-P	GD5210Y -2-5-P	Array	
Package type	TO-46	TO-46	TO-46	LCC3	LCC3	Plastidip	Plastidip	PCB	
Diameter of photosensitive surface(mm)	0.23	0.50	0.80	0.23	0.50	0.23	0.50	Customized	
Spectral response range(nm)	400~1100	400~1100	400~1100	400~1100	400~1100	400~1100	400~1100	400~1100	
Peak response wavelength(nm)	905	905	905	905	905	905	905	905	
Responsiveness $\lambda=905\text{nm}$ $\Phi=1\mu\text{W}$ $M=100$ (A/W)	55	55	55	55	55	55	55	55	
Dark current $M=100$ (nA)	Typical	0.2	0.4	0.8	0.2	0.4	0.2	0.4	According to the photosensitive surface
	Max	1.0	1.0	2.0	1.0	1.0	1.0	1.0	
Response time $\lambda=905\text{nm}$ $R1=50\Omega$ (ns)	0.6	0.6	0.6	0.6	0.6	0.6	0.6	0.6	
Operating voltage temperature coefficient $T=-40^{\circ}\text{C}\sim 85^{\circ}\text{C}$ (V/°C)	0.9	0.9	0.9	0.9	0.9	0.9	0.9	0.9	
Total Capacitance $M=100$ $f=1\text{MHz}$ (pF)	1.0	1.2	2.0	1.0	1.2	1.0	1.2	According to the photosensitive surface	
Breakdown voltage $I_R=10\mu\text{A}$ (V)	Min	130	130	130	130	130	130	130	160
	Max	220	220	220	220	220	220	220	200